

SKM400GA12T4



SEMITRANS® 4

Fast IGBT4 Modules

SKM400GA12T4

Features

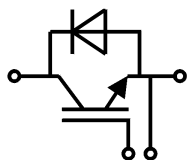
- IGBT4 = 4. Generation (Trench)IGBT
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{Cnom}$
- Soft switching 4. Generation CAL diode (CAL4)
- UL recognized, file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders
- Switched reluctance motor

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ$



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Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	T _j = 175 °C	T _c = 25 °C	616	A
		T _c = 80 °C	474	A
I _{Cnom}			400	A
I _{CRM}	I _{CRM} = 3xI _{Cnom}		1200	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 150 °C	10	μs
T _j			-40 ... 175	°C

Inverse diode

I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	440	A
		$T_c = 80^\circ\text{C}$	329	A
I_{Fnom}			400	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		1200	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$		1980	A
T_j			-40 ... 175	$^\circ\text{C}$

Module

$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$	500	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50 Hz, $t = 1\text{ min}$	4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 400\text{ A}$ $V_{GE} = 15\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$	1.80	2.05	V
		$T_j = 150^\circ\text{C}$	2.20	2.40	V
V_{CE0}	chipllevel	$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$	2.50	2.88	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	3.75	4.00	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 15.2\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
		$T_j = 150^\circ\text{C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	24.6		nF
C_{oes}		$f = 1\text{ MHz}$	1.62		nF
C_{res}		$f = 1\text{ MHz}$	1.38		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		2260		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		1.88		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	240		ns
t_r	$I_C = 400\text{ A}$	$T_j = 150^\circ\text{C}$	56		ns
E_{on}	$V_{GE} = \pm 15\text{ V}$ $R_{G on} = 1\text{ }\Omega$	$T_j = 150^\circ\text{C}$	28		mJ
$t_{d(off)}$	$R_{G off} = 1\text{ }\Omega$	$T_j = 150^\circ\text{C}$	500		ns
t_f	$di/dt_{on} = 7100\text{ A}/\mu\text{s}$ $di/dt_{off} = 3900\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	90		ns
E_{off}		$T_j = 150^\circ\text{C}$	44		mJ
$R_{th(j-c)}$	per IGBT			0.072	K/W



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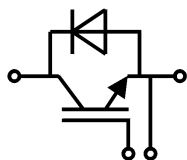
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 400 A	T _j = 25 °C		2.20	2.52	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.15	2.47	V
V _{F0}	chiplevel	T _j = 25 °C		1.3	1.5	V
		T _j = 150 °C		0.9	1.1	V
r _F	chiplevel	T _j = 25 °C		2.3	2.5	mΩ
		T _j = 150 °C		3.1	3.4	mΩ
I _{RRM}	I _F = 400 A	T _j = 150 °C		440		A
Q _{rr}	di/dt _{off} = 7200 A/μs	T _j = 150 °C		78		μC
E _{rr}	V _{GE} = ±15 V V _{CC} = 600 V	T _j = 150 °C		37		mJ
R _{th(j-c)}	per diode				0.14	K/W
Module						
L _{CE}				15	20	nH
R _{CC'+EE'}	terminal-chip	T _C = 25 °C		0.18		mΩ
		T _C = 125 °C		0.22		mΩ
R _{th(c-s)}	per module			0.02	0.038	K/W
M _s	to heat sink M6		3		5	Nm
M _t	to terminals	M6	2.5		5	Nm
		M4	1.1		2	Nm
w					330	g



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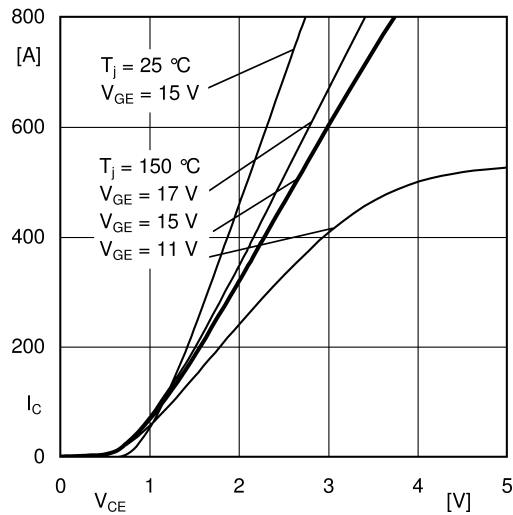


Fig. 1: Typ. output characteristic, inclusive $R_{CC} + EE'$

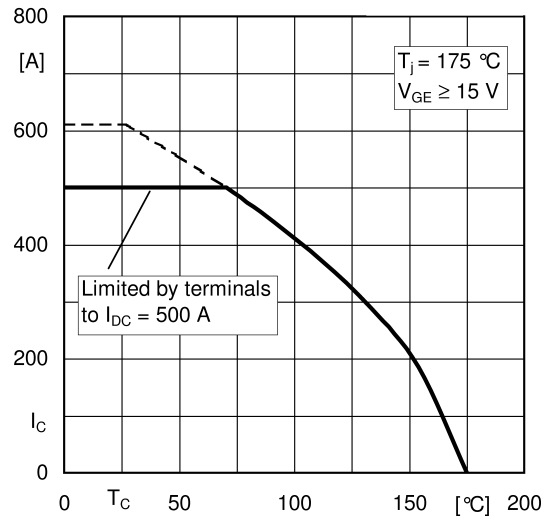


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

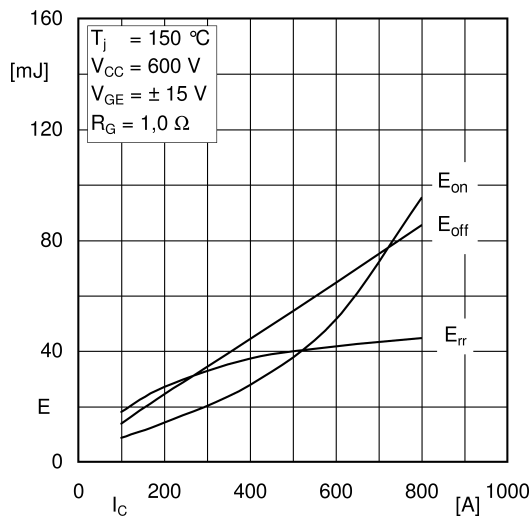


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

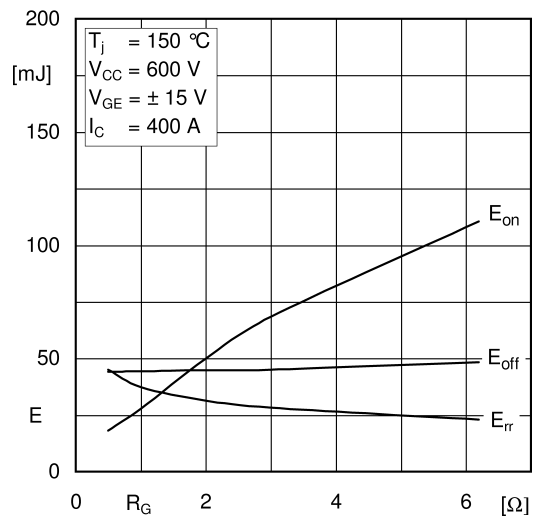


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

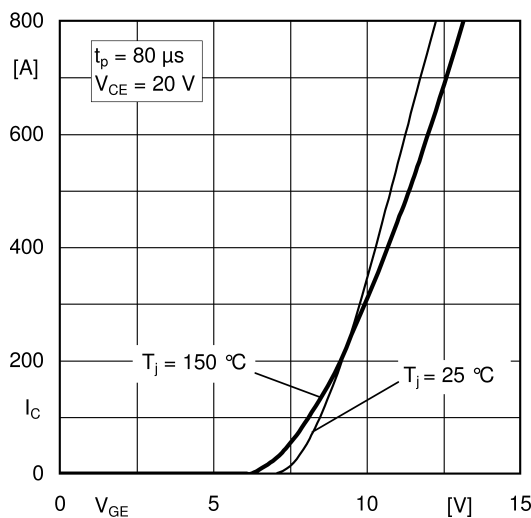


Fig. 5: Typ. transfer characteristic

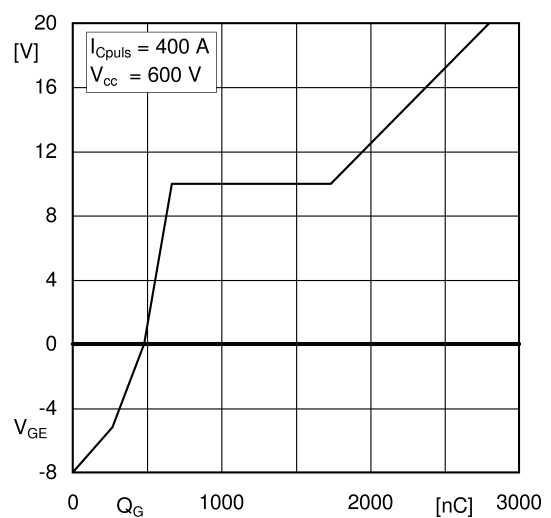


Fig. 6: Typ. gate charge characteristic

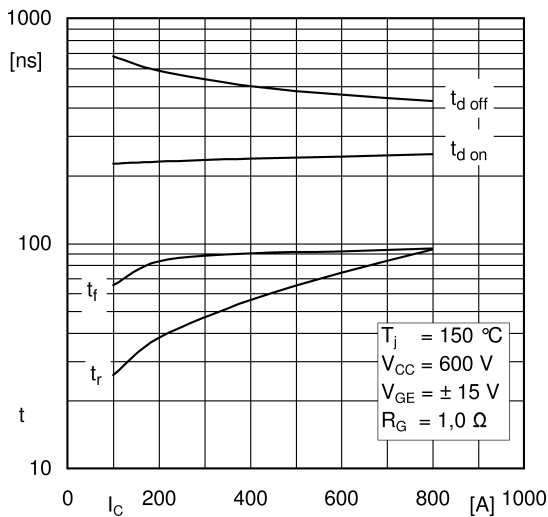


Fig. 7: Typ. switching times vs. I_C

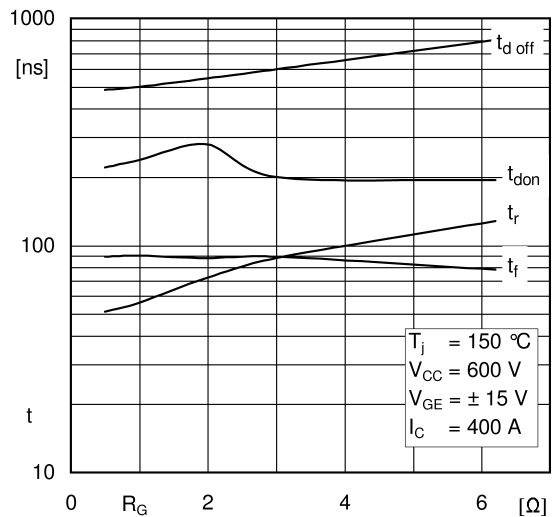


Fig. 8: Typ. switching times vs. gate resistor R_G

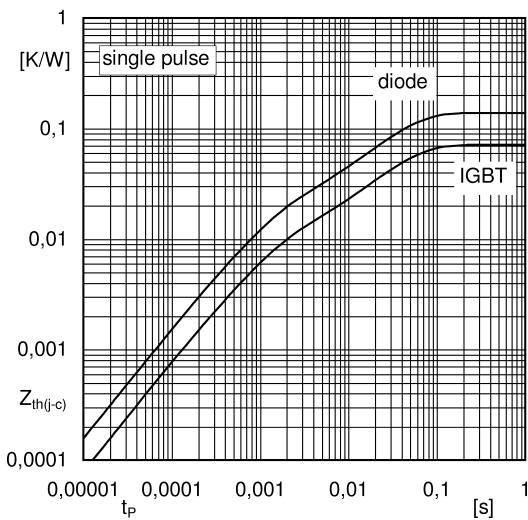


Fig. 9: Transient thermal impedance

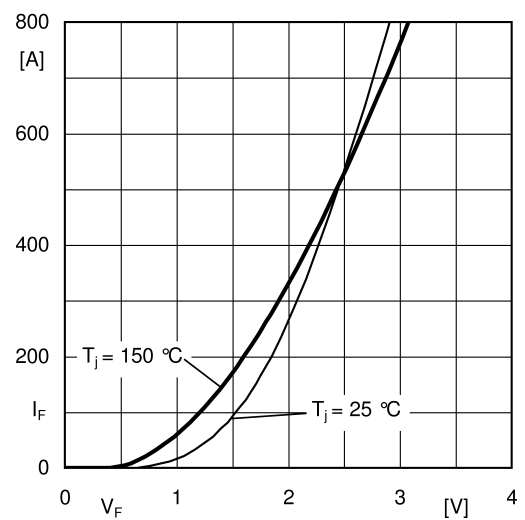


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'}+EE'$

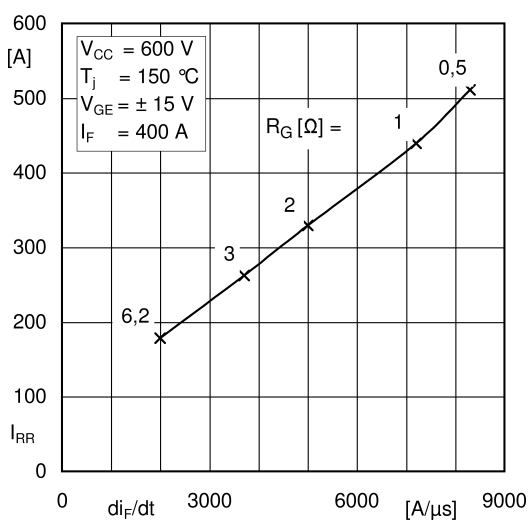


Fig. 11: CAL diode peak reverse recovery current

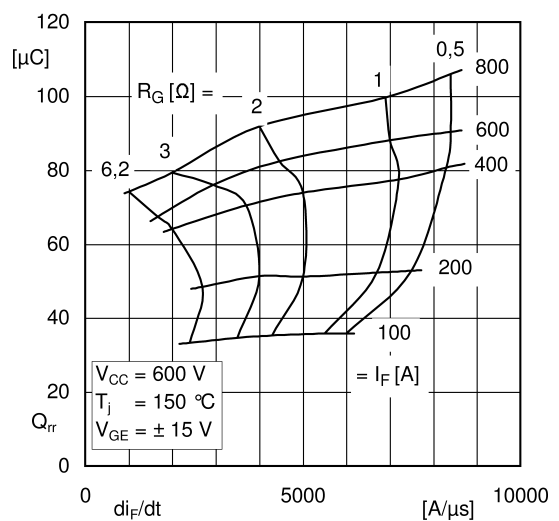
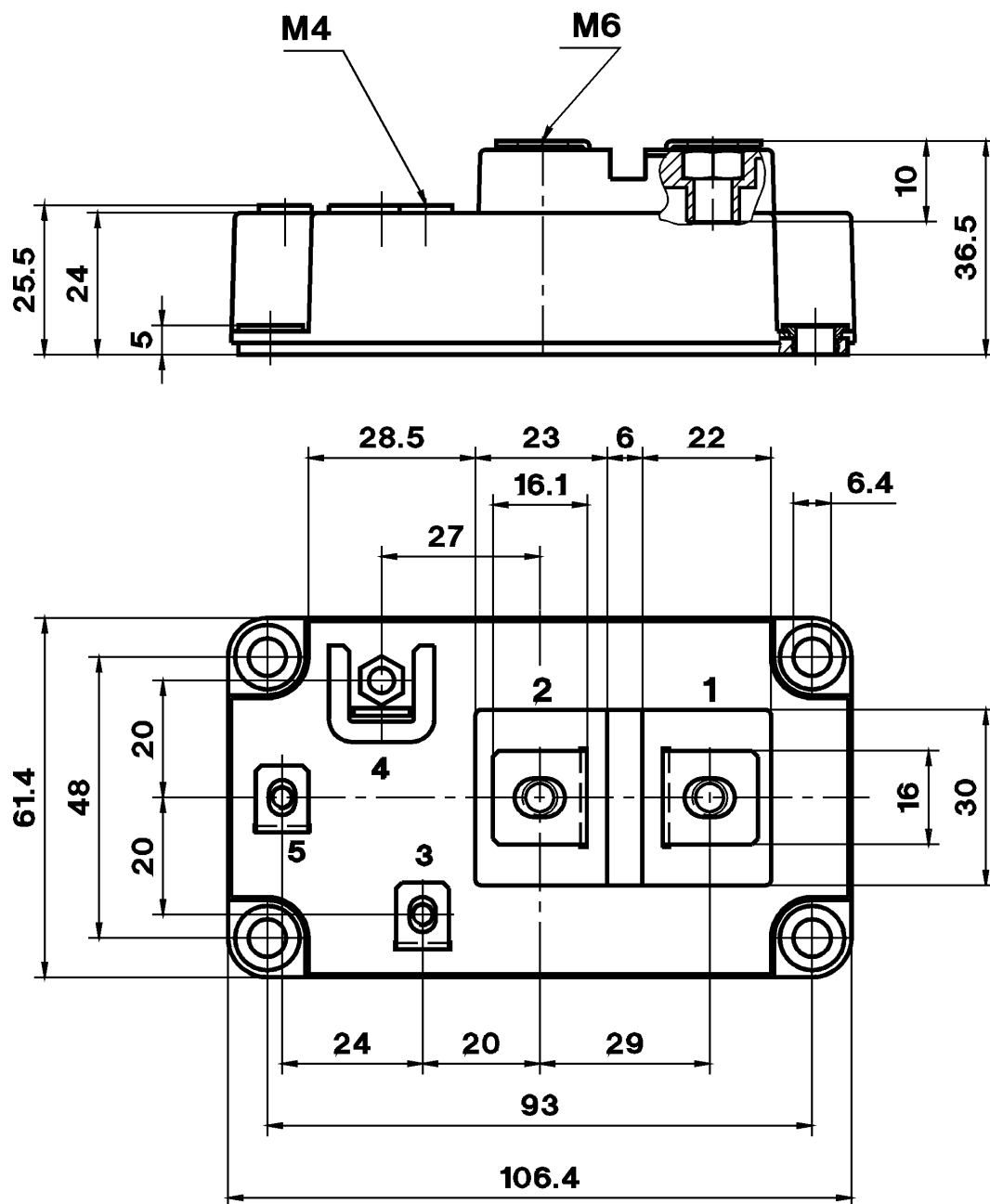
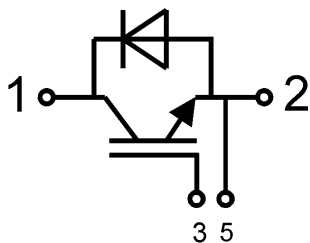


Fig. 12: Typ. CAL diode peak reverse recovery charge



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.